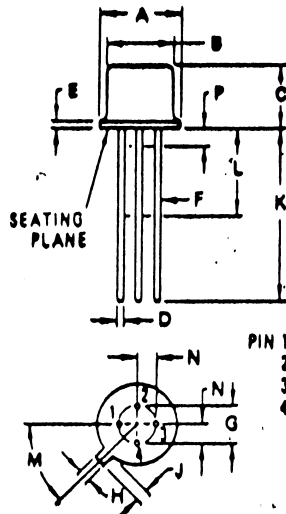


DUAL-GATE MOSFET
N-CHANNEL — DEPLETION



4 TYPE NUMBER	1 BVDSS (V)	2 I(D) RATED MAX (A)	3 PD RATED MAX (W)	DERATE ABOVE 25°C W/°C	FORWARD TRANSCONDUCTANCE				rDS (on) MAX (Ω)	C(iss) MAX (F)	VGS (off) MAX (V)	BVGSS (V)	I(GSS) at VDS=0 (A)	OPER- TE MA °C
					gfs		TEST BIAS							
					MIN (Mhos)	MAX (Mhos)	VGS TEST (V)	VDS TEST (V)						
3N200	20	50m	330m	2.2m	10m%	20m%		15		3.0	6.0	50n	17	



- PIN 1. DRAIN
- 2. GATE 2
- 3. GATE 1
- 4. SOURCE, SUBSTRATE AND CASE

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.31	5.84	0.209	0.230
B	4.52	4.95	0.178	0.195
C	4.32	5.33	0.170	0.210
D	0.41	0.53	0.016	0.021
E	-	0.76	-	0.030
F	0.41	0.48	0.016	0.019
G	2.54 BSC		0.100 BSC	
H	0.91	1.17	0.036	0.046
J	0.71	1.22	0.028	0.048
K	12.70	-	0.500	-
L	8.35	-	0.250	-
M	45° BSC		45° BSC	
N	1.27 BSC		0.050 BSC	
P	-	1.27	-	0.050

ALL JEDEC dimensions and notes apply

PACKAGE OUTLINE DIMENSIONS



Quality Semi-Conductors